Schottky barrier single diodes Rev. 01 — 21 May 2007

Product data sheet

1. Product profile

1.1 General description

Planar Schottky barrier single diodes with an integrated guard ring for stress protection, encapsulated in small Surface-Mounted Device (SMD) plastic packages.

Table 1. **Product overview**

Type number	Package	Package		
	NXP	JEITA	configuration	
RB751CS40	SOD882	-	leadless ultra small	
RB751S40	SOD523	SC-79	ultra small	
RB751V40	SOD323	SC-76	very small	

1.2 Features

- Low forward voltage
- Low capacitance

1.3 Applications

- Ultra high-speed switching
- Voltage clamping
- Line termination
- Reverse polarity protection

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _F	forward current		-	-	120	mA
V _{RRM}	repetitive peak reverse voltage		-	-	40	V
V _F	forward voltage	I _F = 1 mA	<u>[1]</u> _	-	370	mV

[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.



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2. Pinning information

Pin	Description	Simplified outline Symbol
SOD882		
1	cathode	[1]
2	anode	
		sym001
		Transparent top view
SOD323;	SOD523	
1	cathode	[1]
2	anode	
		1 2 sym001
		001aab540

[1] The marking bar indicates the cathode.

3. Ordering information

Type number	Package		
	Name	Description	Version
RB751CS40	-	leadless ultra small plastic package; 2 terminals; body $1.0 \times 0.6 \times 0.5$ mm	SOD882
RB751S40	SC-79	plastic surface-mounted package; 2 leads	SOD523
RB751V40	SC-76	plastic surface-mounted package; 2 leads	SOD323

4. Marking

Table 5. Marking codes

Type number	Marking code
RB751CS40	F6
RB751S40	G4
RB751V40	W8

5. Limiting values

Symbol	Parameter	Conditions	Min	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	40	V
V _R	reverse voltage		-	40	V
I _F	forward current		-	120	mA
I _{FSM}	non-repetitive peak forward current	square wave; t _p < 10 ms	-	200	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u>		
	RB751CS40		[2] _	250	mW
	RB751S40		[2] _	280	mW
	RB751V40		-	280	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

6. Thermal characteristics

Thermal characteristics					
Parameter	Conditions	Min	Тур	Max	Unit
thermal resistance from junction to ambient	in free air	<u>[1]</u>			
RB751CS40		[2] _	-	500	K/W
RB751S40		[2] _	-	450	K/W
RB751V40		-	-	450	K/W
	Parameterthermal resistance from junction to ambientRB751CS40RB751S40	ParameterConditionsthermal resistance from junction to ambientin free airRB751CS40RB751S40	ParameterConditionsMinthermal resistance from junction to ambientin free air[1]RB751CS40[2]-RB751S40[2]-	ParameterConditionsMinTypthermal resistance from junction to ambientin free air[1]RB751CS40[2]RB751S40[2]	ParameterConditionsMinTypMaxthermal resistance from junction to ambientin free air[1]

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

7. Characteristics

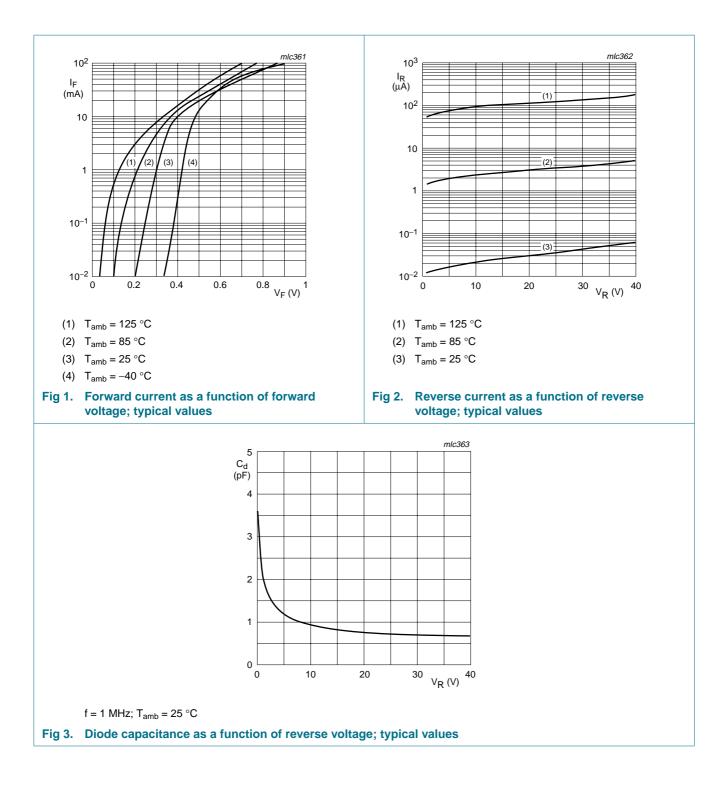
Table 8.Characteristics

 $T_{amb} = 25 \circ C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _F	forward voltage	I _F = 1 mA	<u>[1]</u> _	-	370	mV
I _R	reverse current	V _R = 30 V	-	-	0.5	μΑ
C _d	diode capacitance	V _R = 1 V; f = 1 MHz	-	2	-	pF

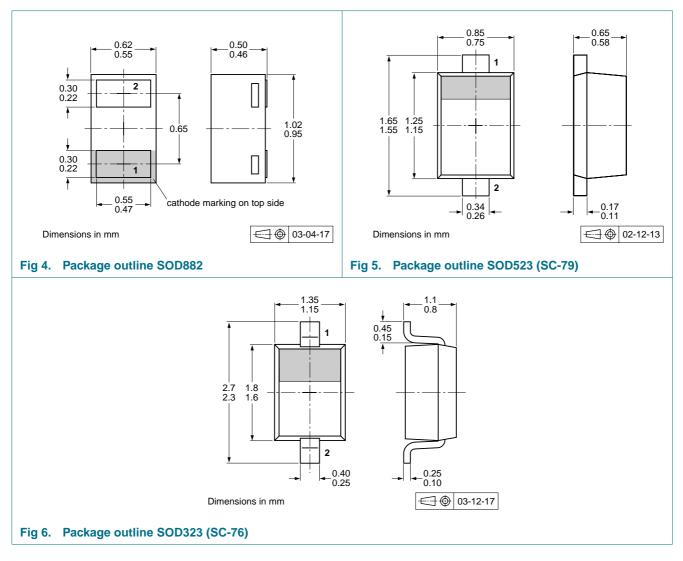
[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.

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8. Package outline



9. Packing information

Table 9.Packing methods

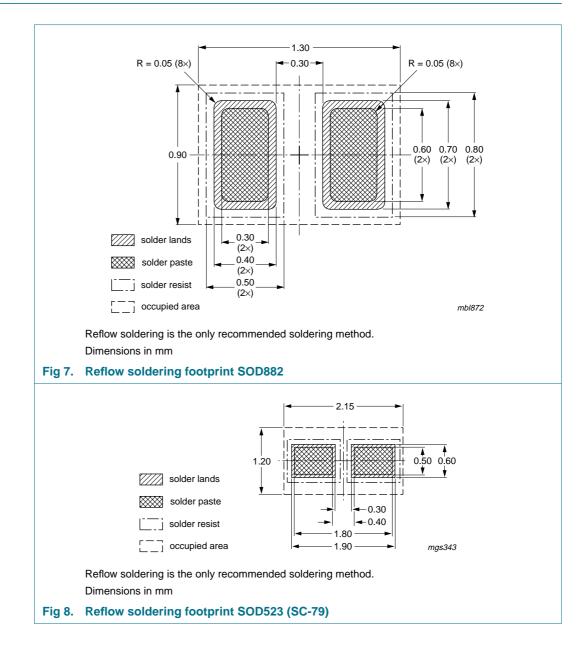
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packin	Packing quantity		
			3000	8000	10000	
RB751CS40	SOD882	2 mm pitch, 8 mm tape and reel	-	-	-315	
RB751S40	RB751S40 SOD523	2 mm pitch, 8 mm tape and reel	-	-315	-	
		4 mm pitch, 8 mm tape and reel	-115	-	-135	
RB751V40	SOD323	4 mm pitch, 8 mm tape and reel	-115	-	-135	

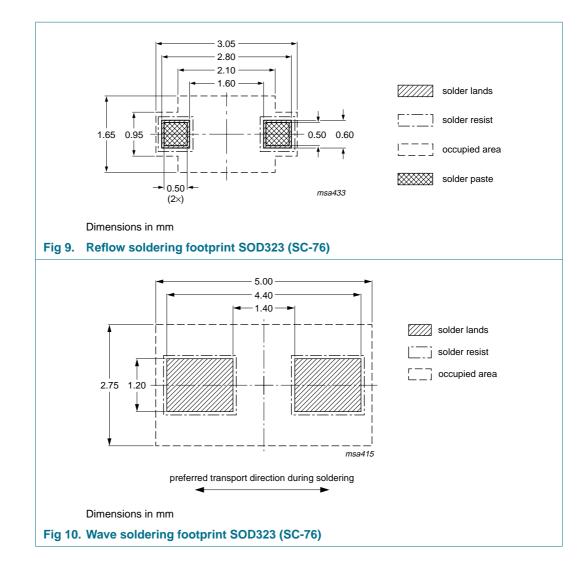
[1] For further information and the availability of packing methods, see <u>Section 13</u>.

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10. Soldering



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RB751_SER_1 Product data sheet

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11. Revision history

Table 10. Revision hist	ory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
RB751_SER_1	20070521	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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